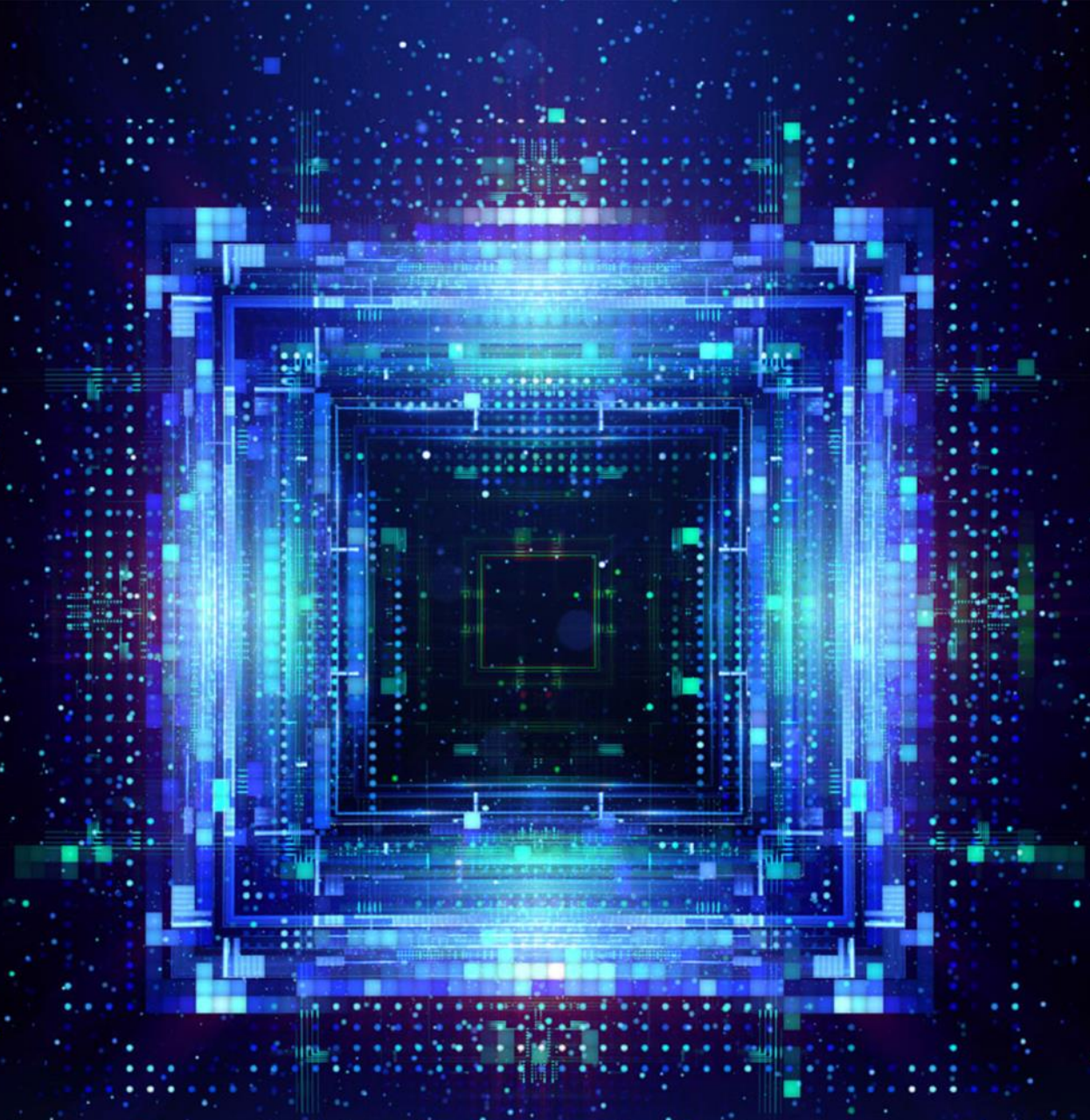


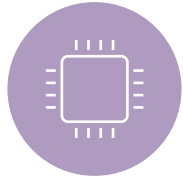


Boosting the efficiency of compound semiconductor devices



Who We Are

Specialized in providing chip-specific custom passivation solutions



Unique expertise in compound semiconductor surface engineering



Proprietary technology that greatly improves the performance and manufacturability of compound semiconductors devices



Contributing to **global environmental sustainability** by improving the efficiency & manufacturing yields of billions of III-V devices

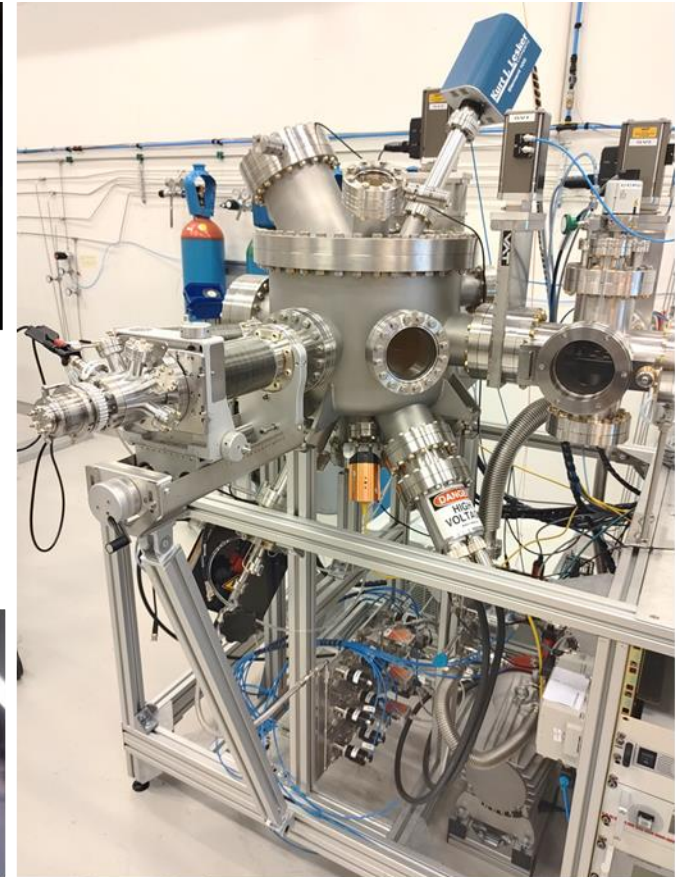
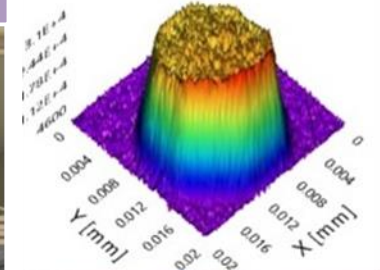
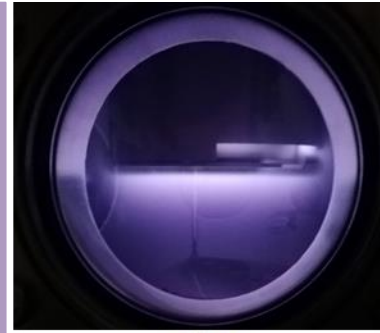


- Incorporated in 2017. Spin-off from University of Turku, Finland
- 17 people
- Own laboratories and HQ in Turku
- 5 granted patent families (27 patents) + 2 new filings
- Extensive processing characterization capabilities for III-V materials



Cutting edge lab

Multiple processing capabilities
3 Kontrox reactors



State-of-the-art characterization techniques



Characterization

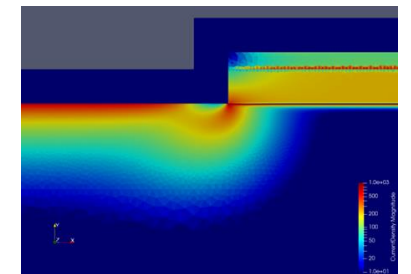
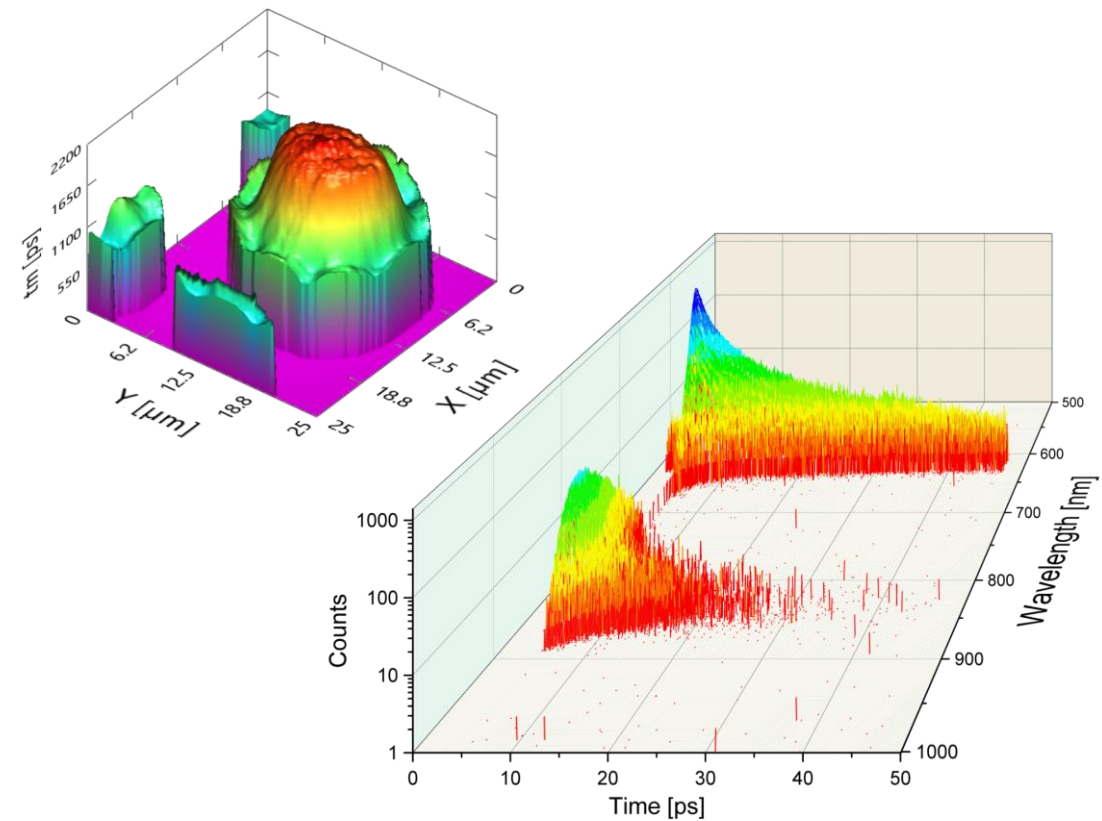
Semiconductor device and materials

- LIV
- C-V
- Auger Electron Spectroscopy / XPS
- SEM/EDX
- Cathodoluminescence
- Reflection High Energy Electron Diffraction (RHEED) & Low Energy Electron Diffraction (LEED)
- Mass spectrometry, UV-VIS spectroscopy
- SPM / HR-TEM

Advanced optical techniques and proprietary hardware for optoelectronic devices

- Multiple inspections in one tool: PL and TCSPC (carrier lifetime), combined with wavelength resolved measurements for in-depth chip characterization
- Outstanding resolution and high-speed measurements
- Full wafer or single pixel characterization

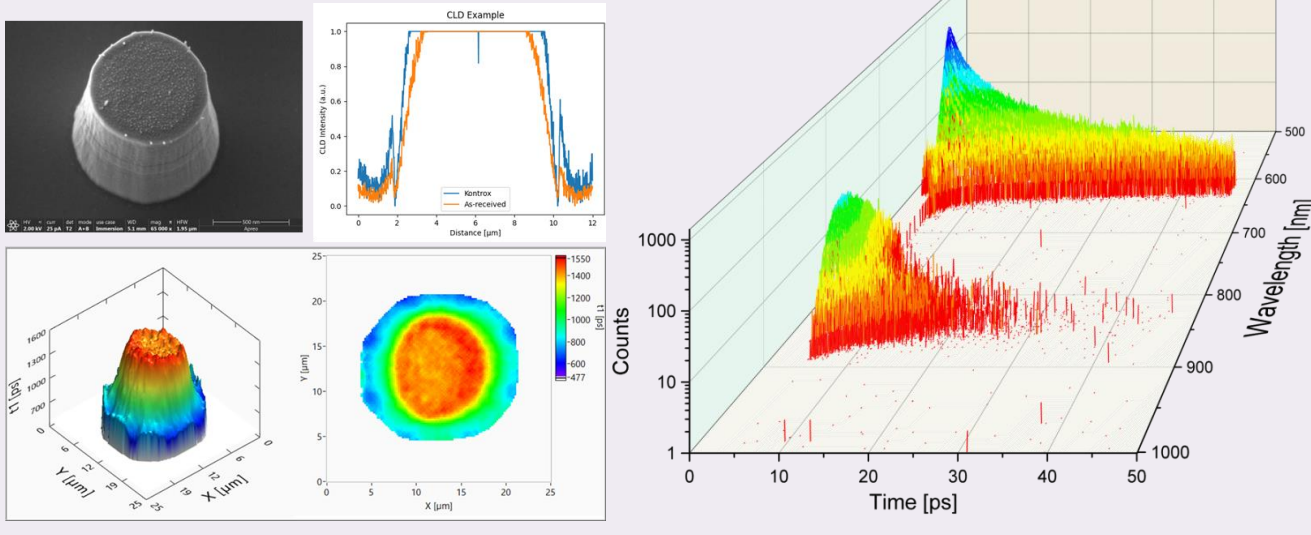
Multiscale TCAD simulations



Characterization

Advanced optical techniques and proprietary hardware for optoelectronic devices

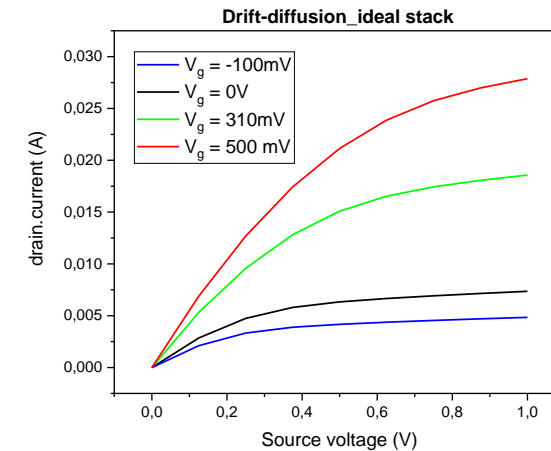
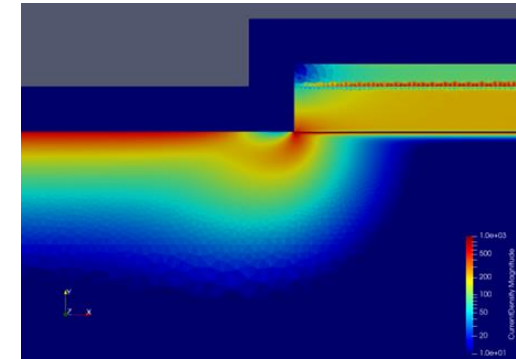
- Multiple inspections in one tool: PL and TCSPC (carrier lifetime), combined with wavelength resolved measurements for in-depth chip characterization
- Outstanding resolution and high-speed measurements
- Full wafer or single pixel characterization



Semiconductor Device And Materials

- LIV
- C-V
- Auger Electron Spectroscopy / XPS
- SEM/EDX
- Cathodoluminescence
- Reflection High Energy Electron Diffraction (RHEED) & Low Energy Electron Diffraction (LEED)
- Mass spectrometry, UV-VIS spectroscopy
- SPM / HR-TEM

Multiscale TCAD simulations



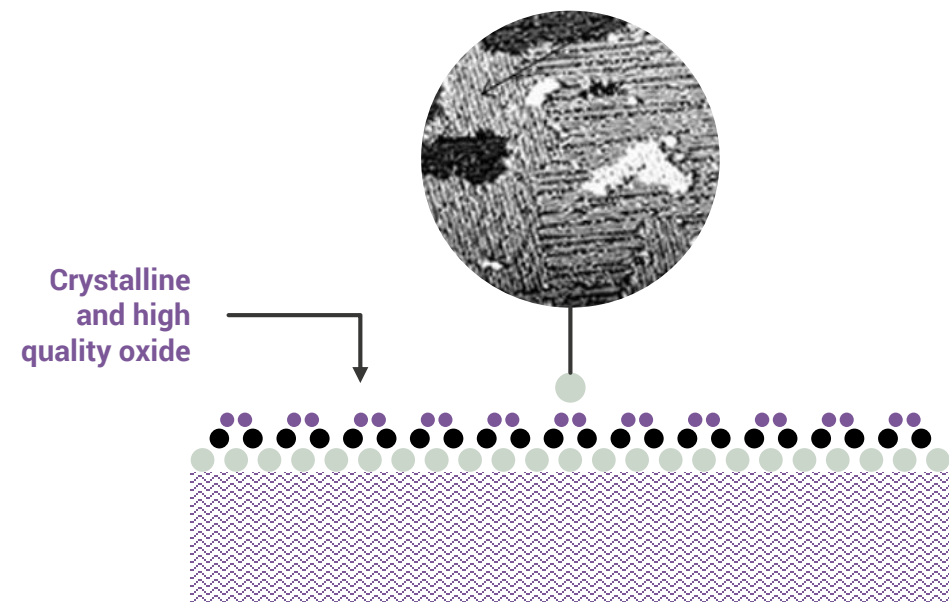
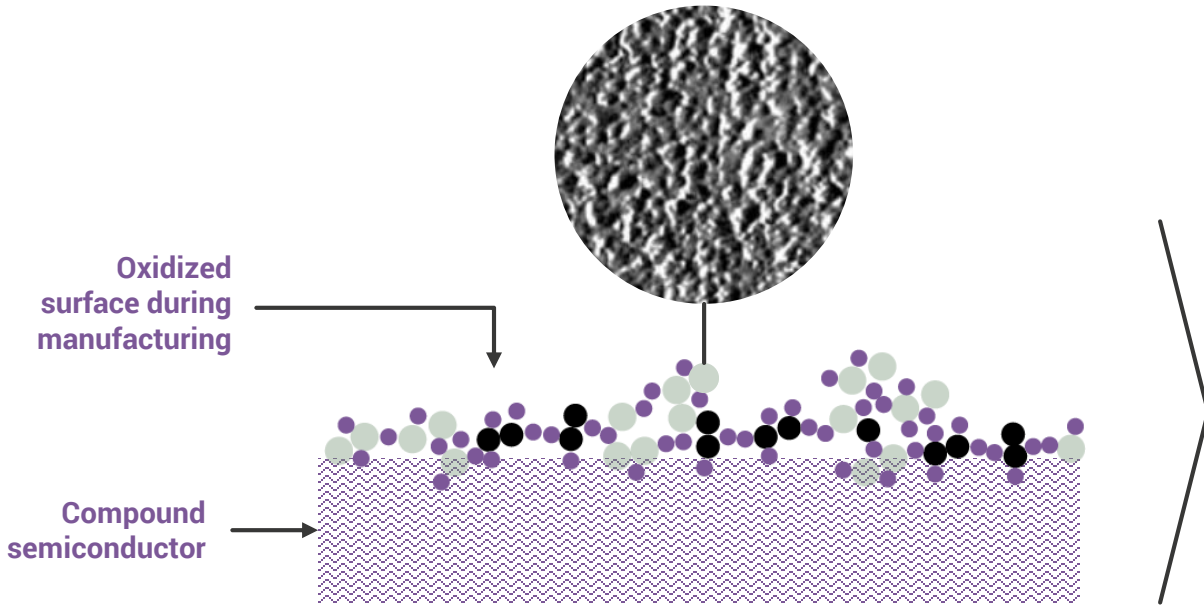
Why Comptek

Kontrox™

Breakthrough nanoengineering technology

Existing technologies result in high density of atomic level defects

Defect free surfaces

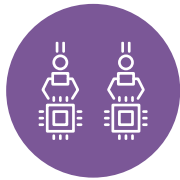


1st time ever to control oxidation in compound semiconductor materials

- 98% less defects
- Unprecedented device performance
- Higher manufacturing yields



Performance drops



Low Yields

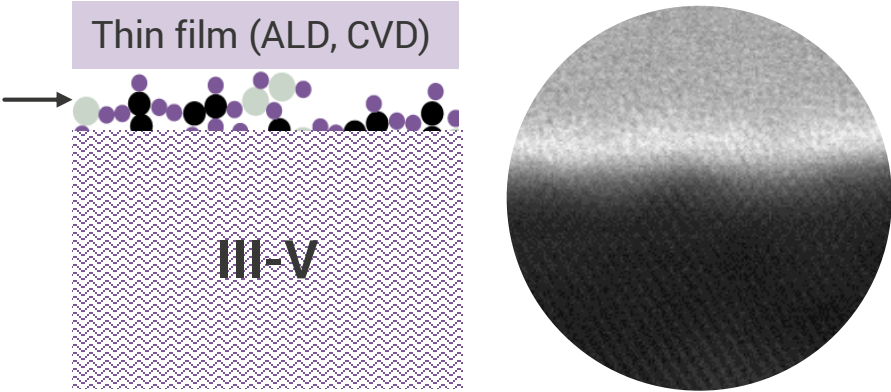


High Costs

Complementing Traditional Methods

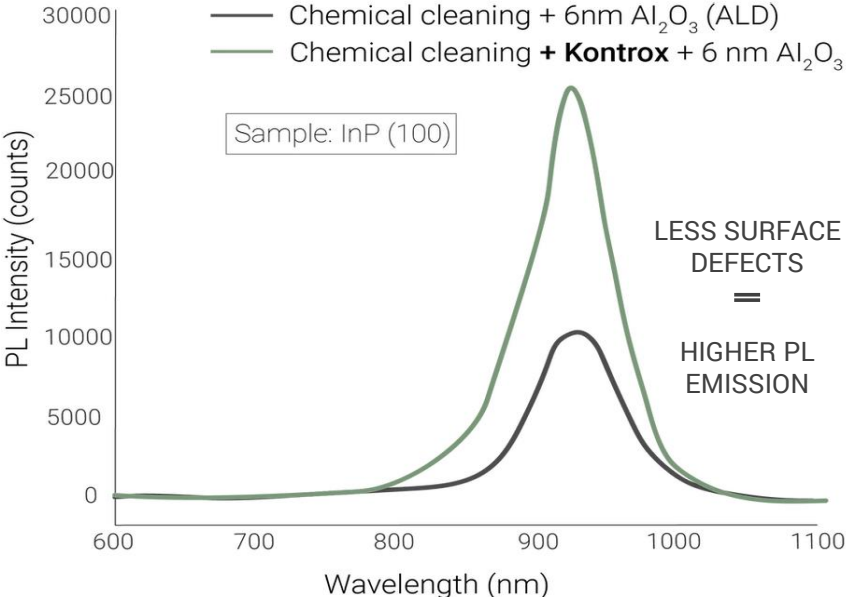
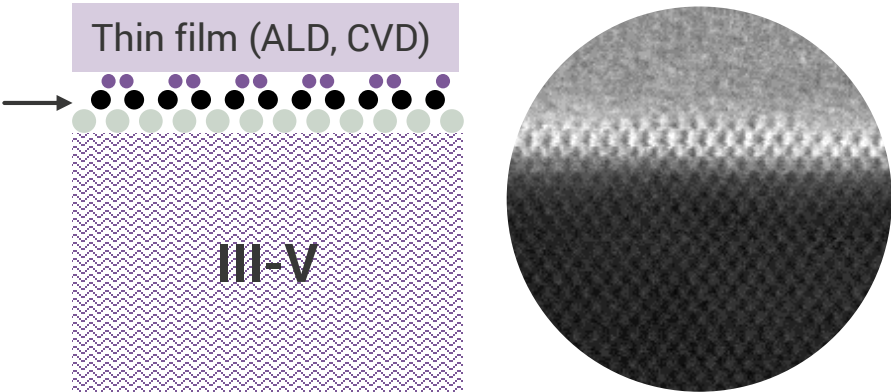
Interfaces between III-V material and traditional thin films still presents high density of defects.

Interface gets oxidized during the first steps of the thin film deposition



Kontrox™ complements and improves conventional methods to enable the next generation of compound semiconductor devices

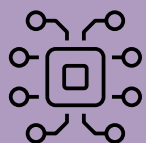
KONTROX high quality oxide stable during thin film deposition



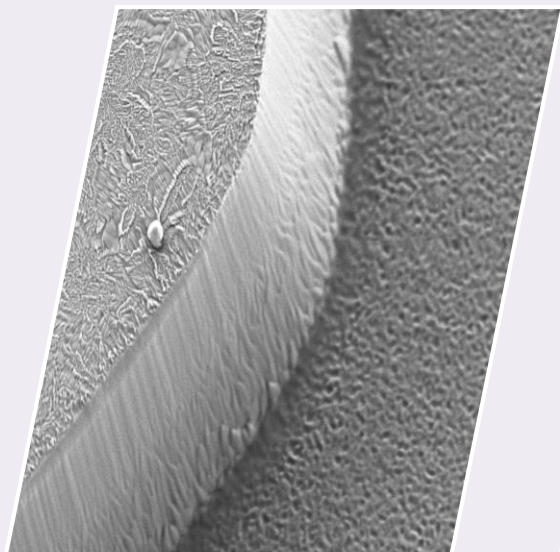
Best-in-class Interfaces

Kontrox™ + ALD/CVD

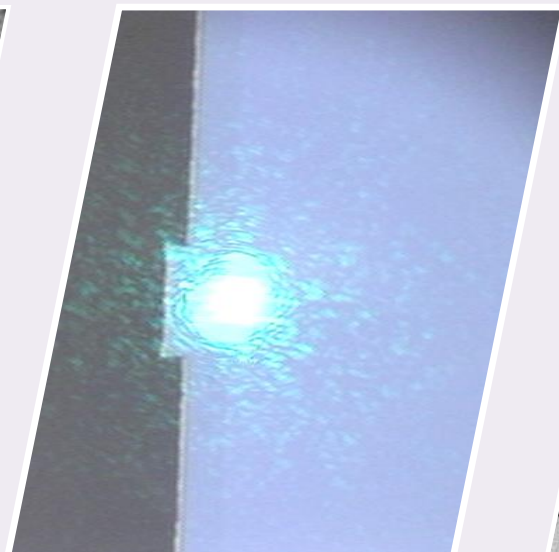
Applications



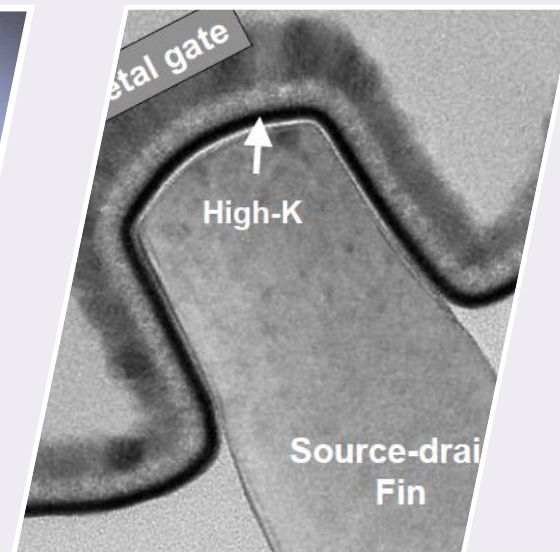
GaAs AlGaAs InAs InGaAs InAlGaAs InP GaSb InSb InGaP GaP
InGaAlP GaN InGaN AlGaN & more



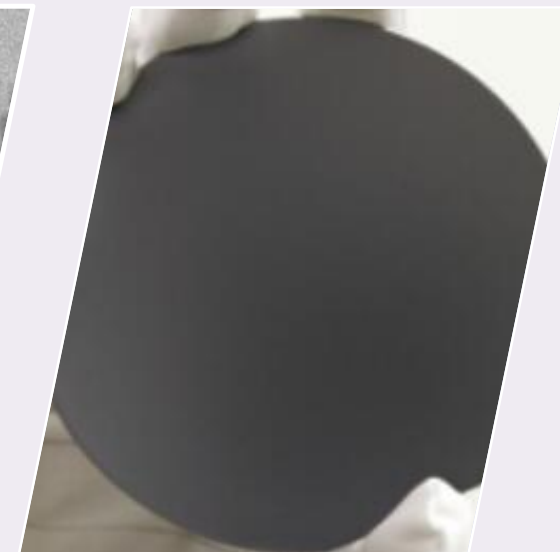
Mesa
Sidewalls



Laser
Facets



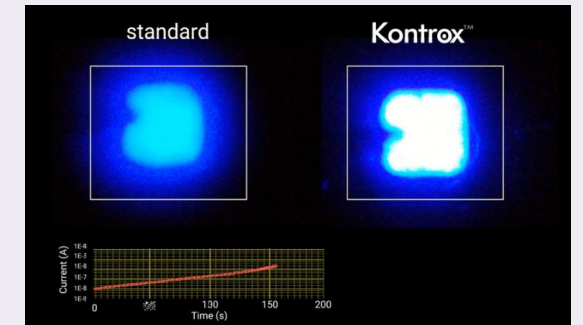
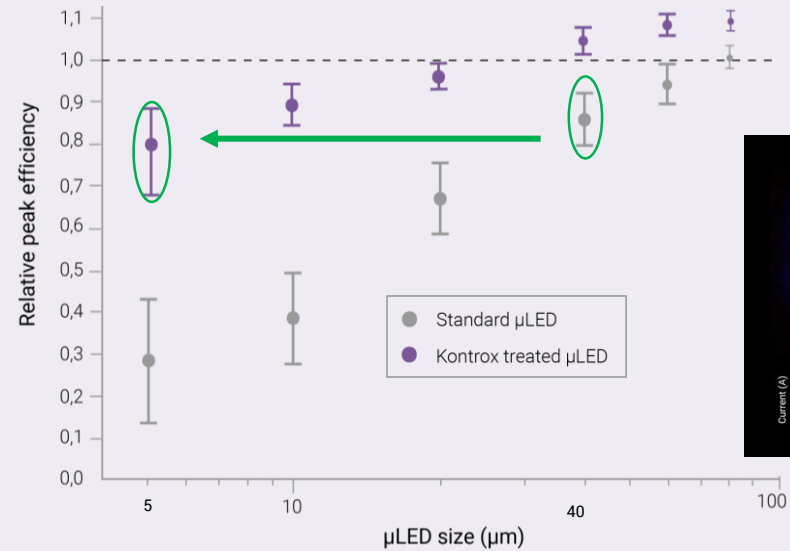
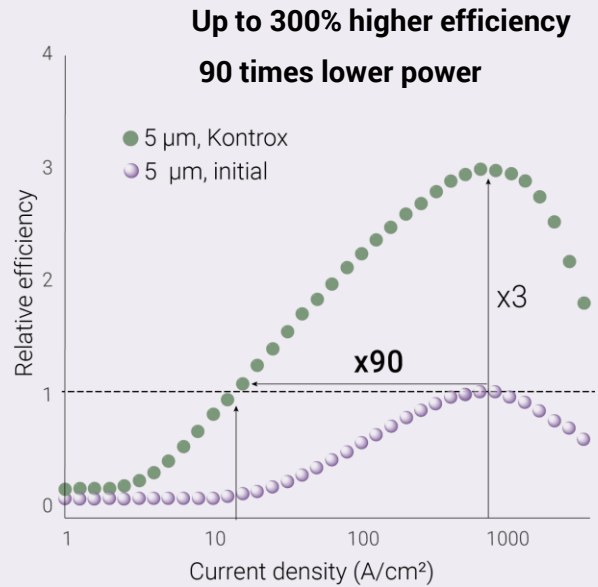
Transistor
based



III-V
Substrates

Technology Proven with Several Industrial Players

Application case example: μ LEDs



Important chip size reduction opportunity

- 5 μ m chip can perform as good as a 40 μ m.
- **10 times more microLED chips/wafer**



**Reduction of
production
volumes / Costs**

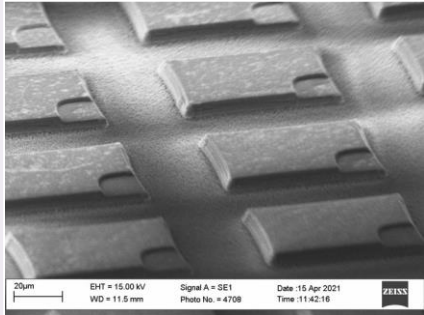


**Less
natural resources
& electricity**

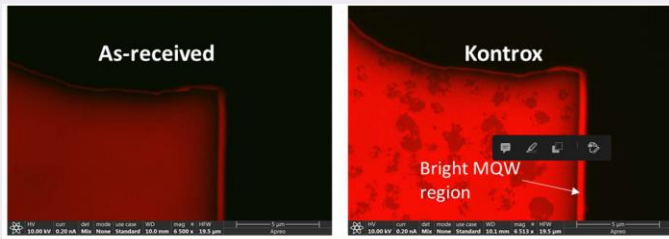


**Less
waste**

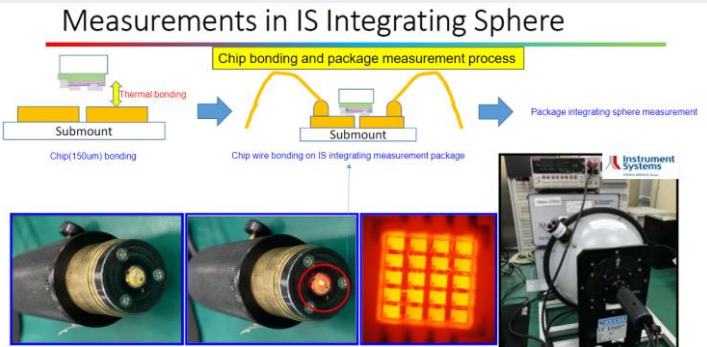
Example of device improvements Kontrox vs Thin films



Mini/microLEDs in size 45x60µm. InGaAlP based.
2.5x wall plug efficiency improvements obtained by Kontrox vs ALD / CVD passivations

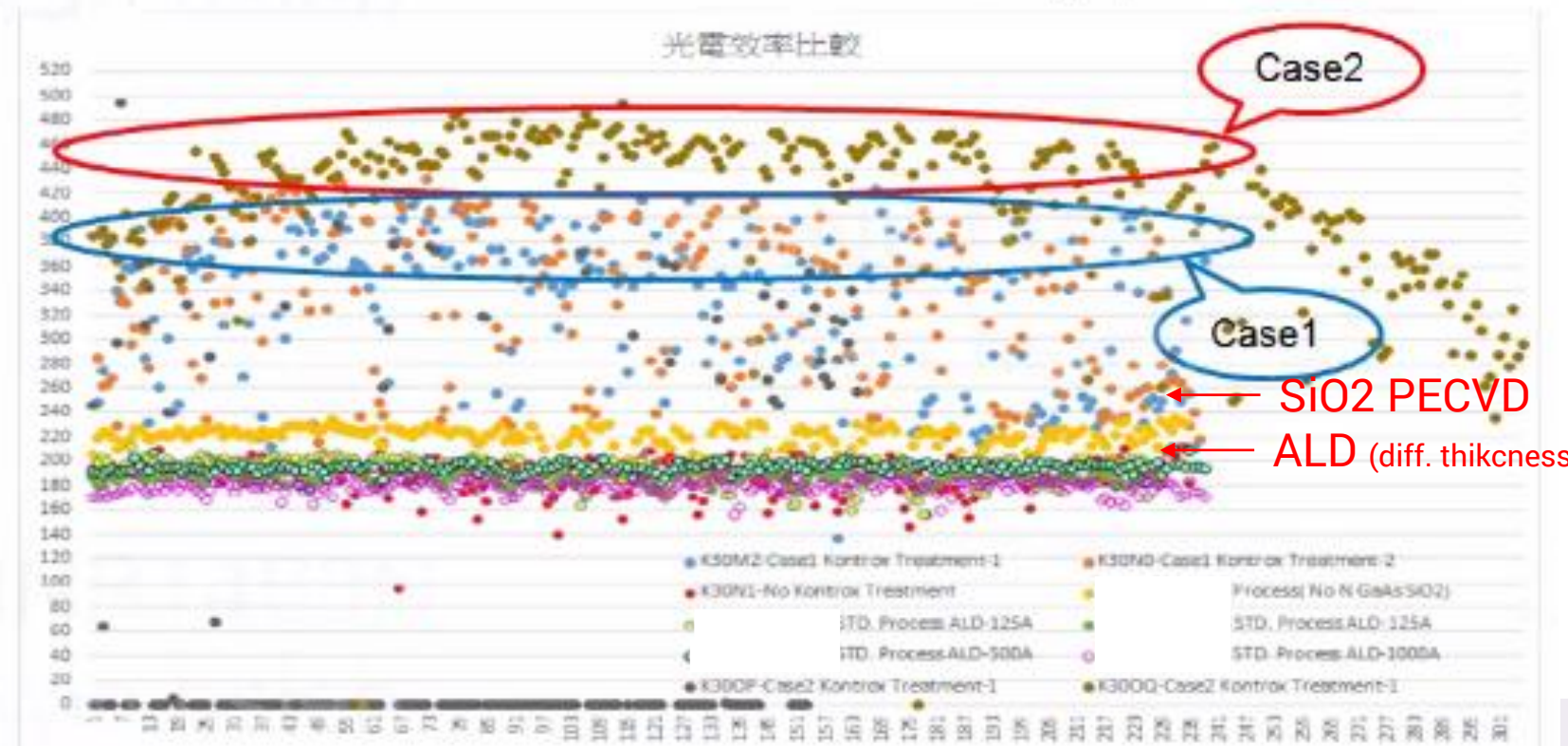


Cathodoluminescence images measured with identical parameters



EL measurements on Wafer – Efficiency

$$WPE = LOP / (I \times V) \quad *LOP \text{ is not calibrated}$$

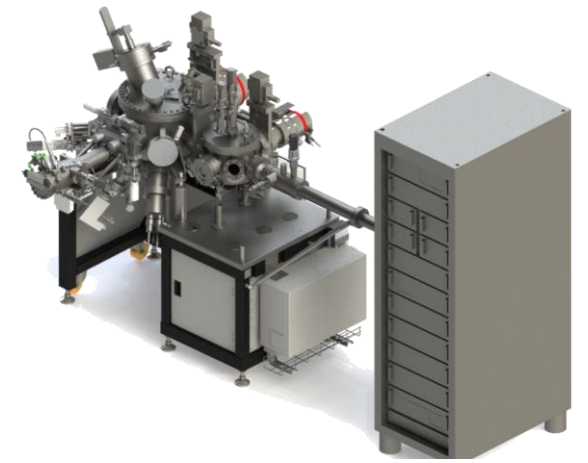


Kontrox for edge-emitting laser facets

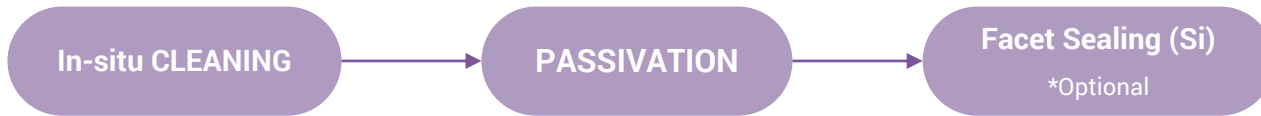
Highest Quality / Cost-of-Ownership ratio available in the market

Kontrox vs existing methods:

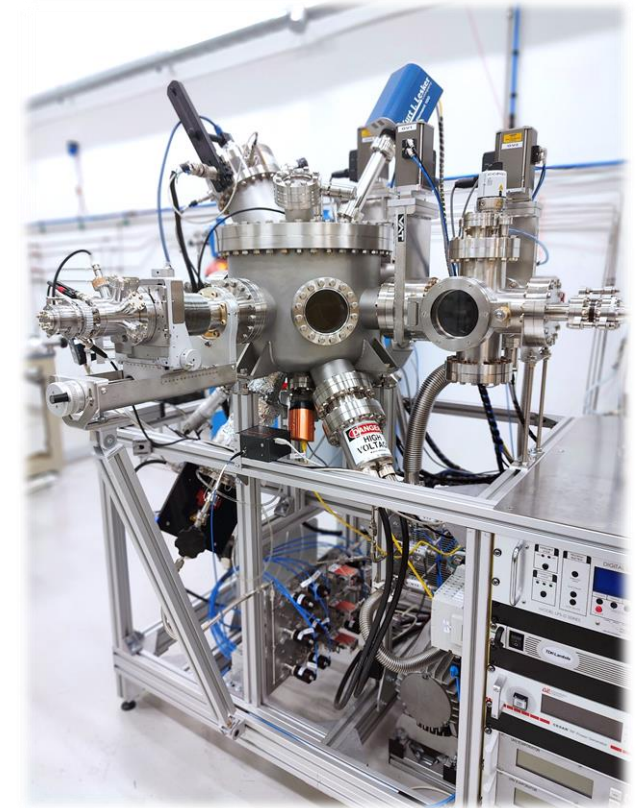
Feature \ Method	a:Si coating, Si (industry standard)	E2 (cleaning in UHV)	Kontrox™
Quality	✓	✓✓✓	✓✓
Quality for Al-containing lasers	✗	✓✓	✓✓
Cost	\$	\$\$\$\$	\$\$
Drawbacks	Defects not fully avoided	Very low throughput	New technology



Easy implementation: One single chamber machine



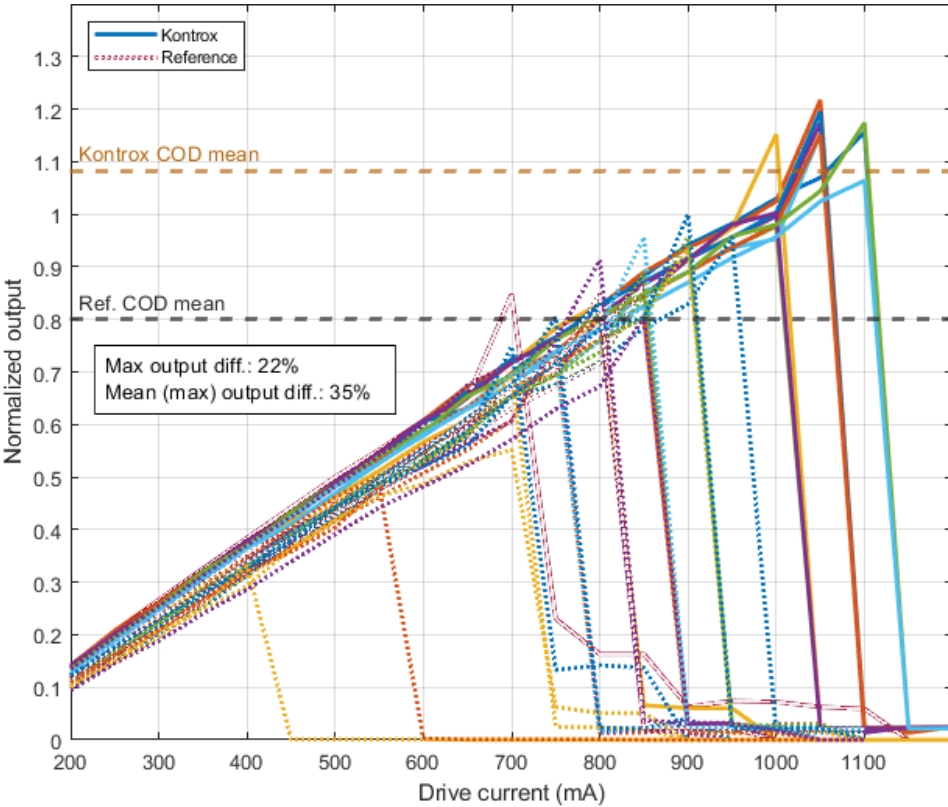
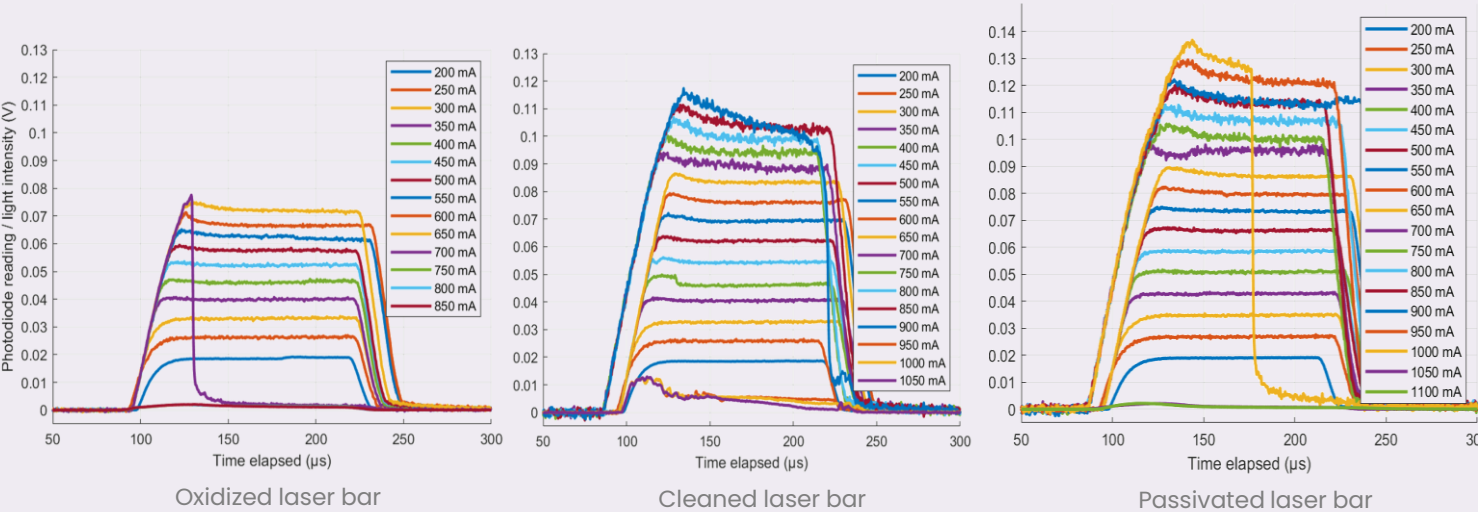
- In-situ cleaning + passivation of both facets
- Stable passivation (i.e. longtime exposure to air prior mirror coatings)
- Fully automated machine designed and built in the EU
- High throughput. Up to 1800 bars/ day



Example of COD improvements in edge-emitting laser facets

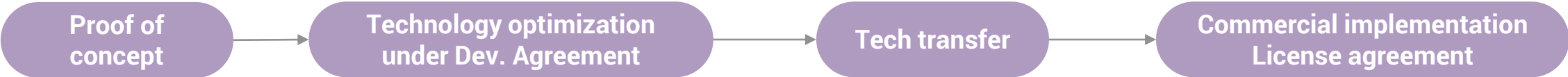
- Laser bars GaAs/AlGaAs based with Al:45%
- Wavelength 770nm

LIV measurements of laser bars: oxidized, cleaned and passivated (*No mirror coatings)



Business Model: Technology transfer and licensing

Tailored Turnkey KONTRON solutions to improve customer's chip performance and manufacturing



Thank You



**In search of improved
performance?**

Comptek Solutions is your partner

For more information

Please contact us at
info@comptek-solutions.com

Vicente Calvo Alonso
CEO & Founder
vicente.calvo@comptek-solutions.com
+358442404004